

#### 40V P-CHANNEL ENHANCEMENT MODE MOSFET POWERDI<sup>®</sup>

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-40V	11mΩ @ V <sub>GS</sub> = -10V	-17.0A
-40 V	15mΩ @ V <sub>GS</sub> = -4.5V	-14.5A

## **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test In Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Description**

This new generation MOSFET has been designed to minimize the onstate resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management

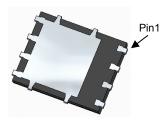
## **Applications**

- DC-DC Converters
- Power management functions
- Analog Switch

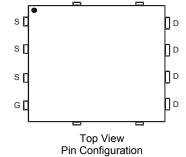
#### **Mechanical Data**

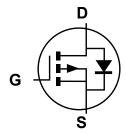
- Case: POWERDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (approximate)





**Bottom View** 





Internal Schematic

Top View

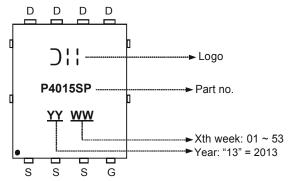
## Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
DMP4015SPS-13	Standard	POWERDI®5060-8	2,500 / Tape & Reel
DMP4015SPSQ-13	Automotive	POWERDI <sup>®</sup> 5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.
- 5. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.

### **Marking Information**





## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	-40	V		
Gate-Source Voltage	$V_{GSS}$	±25	V		
Continuous Drain Current (Note 6) V - 40V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ΙD	-8.5 -6.8	Α
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-13.0 -10.5	Α
Continuous Drain Correct (Note 7) V - 40V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-11.0 -8.7	Α
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-17.0 -13.5	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-100	Α		
Maximum Body Diode Continuous Current (Note 7)			I <sub>S</sub>	-3.5	Α
Avalanche Current (Note 8)			las	-22	Α
Avalanche Energy (Note 8)			E <sub>AS</sub>	242	mJ

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	C	1.3	W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	$P_{D}$	0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D	96.4	°C/W
Thermal Resistance, Junction to Ambient (Note o)	t<10s	$R_{\theta JA}$	40.6	°C/W
Total Dayor Dissination (Note 7)	T <sub>A</sub> = +25°C	0	2.1	W
Total Power Dissipation (Note 7)	T <sub>A</sub> = +70°C	P <sub>D</sub>	1.4	
Thermal Desistance, Junction to Ambient (Note 7)	Steady state	0	55.0	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	24.0	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	4.15	°C/W	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

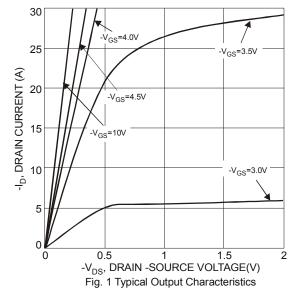
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40		_	V	$V_{GS} = 0V$ , $I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		-	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.5	-2.0	-2.5	<b>V</b>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D		7	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		9	15	11122	$V_{GS} = -4.5V$ , $I_D = -9.8A$	
Forward Transfer Admittance	Y <sub>fs</sub>		26	_	S	V <sub>DS</sub> = -20V, I <sub>D</sub> = -9.8A	
Diode Forward Voltage	$V_{SD}$		-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	4234	_		.,	
Output Capacitance	Coss	_	1036	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		526	_			
Gate Resistance	$R_G$		7.77	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	$Q_g$		47.5	_		V - 20V V - 5V	
Gate-Source Charge	Qgs		14.2	_	nC	$V_{DS} = -20V, V_{GS} = -5V$ $I_{D} = -9.8A$	
Gate-Drain Charge	$Q_{gd}$	_	13.5	_			
Turn-On Delay Time	t <sub>D(on)</sub>		13.2	_			
Turn-On Rise Time	t <sub>r</sub>	_	10.0	_	no	$V_{GS} = -10V$ , $V_{DD} = -20V$ , $R_G = 6\Omega$ ,	
Turn-Off Delay Time	t <sub>D(off)</sub>		302.7		ns	$I_D = -1A, R_L = 20\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	137.9	_			

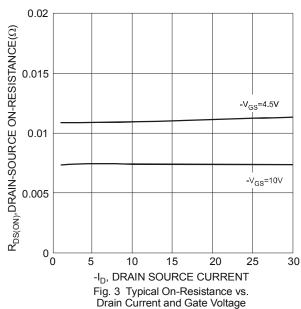
Notes:

- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
- 8. UIS in production with L = 0.1mH, TJ = +25°C
- 9 .Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to production testing.

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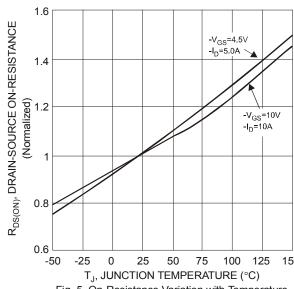
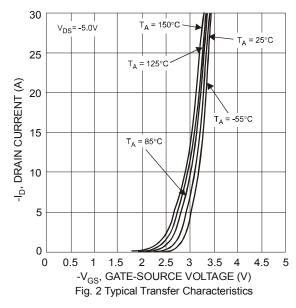
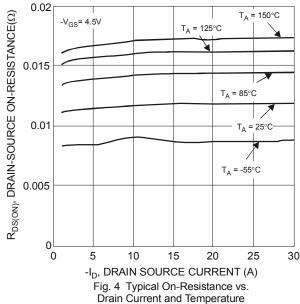


Fig. 5 On-Resistance Variation with Temperature





0.02  $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ -V<sub>GS</sub> = 4.5V 0.016 -I<sub>D</sub> = 5.0A 0.012 V<sub>GS</sub> = 10V 0.008 I<sub>D</sub> = 10A 0.004 0 <u></u> 25 50 75 100 125 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)



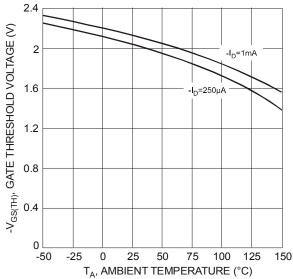
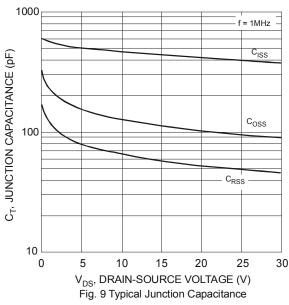
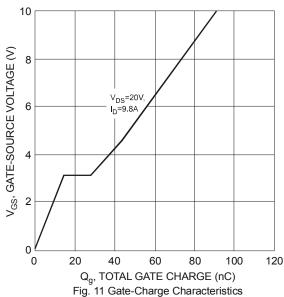
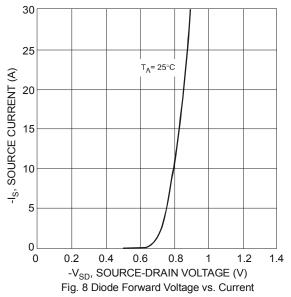


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







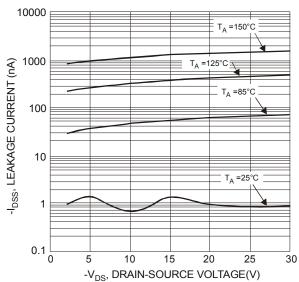


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

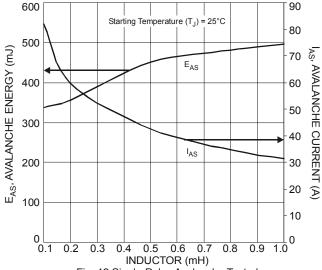
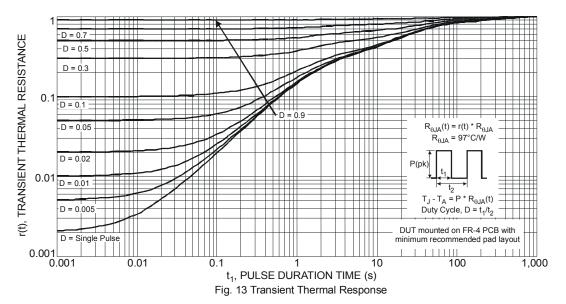


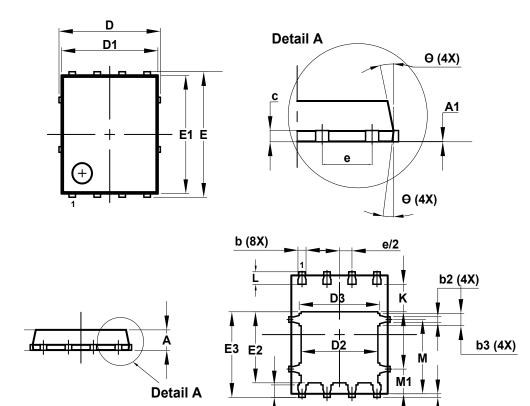
Fig. 12 Single-Pulse Avalanche Tested





## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



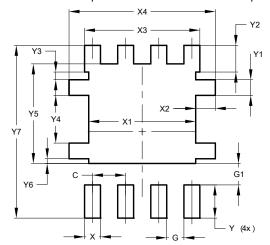
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POWERDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
<b>A</b> 1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	5	.15 BS	0		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	_		
L	0.51	0.71	0.61		
L1	0.050	0.20	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					



#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			

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